



Product data sheet

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SOT-323

BAV99W SWITCHING DIODE

FEATURES

- For high-speed switching applications
- Connected in series

MARKING: KJG

Maximum Ratings @Ta=25℃

Parameter	Symbol	Limit	Unit
Reverse Voltage	V _R	75	V
Forward Current	I _F	150	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	I _{FSM}	2.0	А
Power Dissipation	PD	200	mW
Thermal Resistance Junction to Ambient	R _{θJA}	625	°C/W
Junction Temperature	TJ	150	°C
Storage Temperature range	T _{STG}	-55~+150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	V _(BR)	I _R = 100μA	75		V
Reverse voltage leakage current	I _{R1}	V _R =75V		2.5	μA
	I _{R2}	V _R =25V		25	nA
Forward voltage	V _F	$I_F=1mA$ $I_F=10mA$ $I_F=50mA$ $I_F=150mA$		715 855 1000 1250	mV
Diode capacitance	CD	V _R =0 f=1MHz		2	pF
Reverse recovery time	trr	$I_F = I_R = 10 \text{mA}$ $I_r = 0.1 \times I_R, R_L = 100 \Omega$		4	ns





BAV99W

Semiconductor

HF

Compiance

RoHS





PACKAGE MECHANICAL DATA







Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
A	0.900	1.100	0.035	0.043	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.000	0.035	0.039	
b	0.200	0.400	0.008	0.016	
С	0.080	0.150	0.003	0.006	
D	2.000	2.200	0.079	0.087	
E	1.150	1.350	0.045	0.053	
E1	2.150	2.450	0.085	0.096	
е	0.650) TYP	0.026	6 TYP	
e1	1.200	1.400	0.047	0.055	
L	0.525 REF		0.021 REF		
L1	0.260	0.460	0.010	0.018	
θ	0°	8°	0°	8°	

Suggested Pad Layout



Note:

1.Controlling dimension:in millimeters.

2.General tolerance:±0.05mm.

3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
BAV99W	SOT-323	3000





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